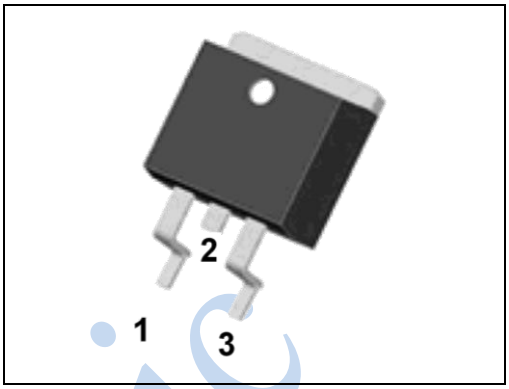
N-Channel 100 V MOSFET

TO263-3L



Product summary

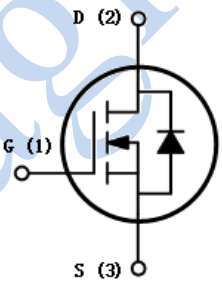
V_{DS} (V)	$R_{DS(on),max}$ (mΩ)	I_D (A)
100	2.7 @ V_{GS} = 10V	166 (1)

Features

- Low $R_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

Applications

- DC/DC conversion
- Power switch
- Motor drives



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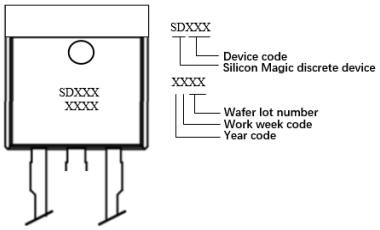


Package and ordering information

Ordering code	Package	Device code
SDH10N2P7S2B	TO263-3L	AGC

1. Maximum ratings

Absolute maximum ratings (T_A = 25℃ unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-source voltage		V_{DS}	100	V
Gate-source voltage		V_{GS}	±20	
Continuous drain current	T_C=25℃ (1)	I_D	166	A
	T_C=100℃		162	
	T_A=25℃ (4)		25	
Pulsed drain current(2)		$I_{D,pulse}$	664	
Avalanche energy, single pulse(3)		E_{AS}	629	mJ
Power dissipation	T_C=25℃	P_D	300	W
	T_A=25℃ (4)		3.7	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to 175	℃

2. Thermal resistance ratings

Thermal resistance ratings				
Parameter		**Symbol**	**Max.**	**Unit**
Thermal resistance, junction-to-case	Steady state	$R_{\theta JC}$	0.5	℃/W
Thermal resistance, junction-to-ambient (4)	Steady state	$R_{\theta JA}$	40	

3. Electrical Characteristics

Electrical characteristics						
Parameter	**Symbol**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static parameter						
Drain to source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0, I_D = 250 μA	100			V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2.2	3	3.8	V
Gate-body leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			1	μA
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 25 A		2.4	2.7	mΩ
Forward transconductance (5)	g_{fs}	V_{DS} = 5 V, I_D = 25 A		102		S
Gate resistance	R_g	f = 1 MHz		1	2	Ω
Dynamic (5)						
Total gate charge	Q_g	V_{DS} = 50 V, I_D = 25 A, V_{GS} = 10 V		150	210	nC
Gate-source charge	Q_{gs}			32	45	
Gate-drain charge	Q_{gd}			45	63	
Turn-on delay time	$t_{d(on)}$	V_{DS} = 50 V, I_D = 25 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		46	92	ns
Rise time	t_r			48	96	
Turn-off delay time	$t_{d(off)}$			132	264	
Fall time	t_f			68	136	
Input capacitance	C_{iss}	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz		8400	11760	pF
Output capacitance	C_{oss}			1150	1610	
Reverse transfer capacitance	C_{rss}			26	52	
Reverse Diode Characteristics (5)						
Diode forward voltage	V_{SD}	V_{GS} = 0 V, I_F = 25 A		0.8	1.1	V
Reverse recovery time	t_{rr}	V_{DS} = 50 V,I_F = 25 A, di/dt = 100 A/μs		90	162	ns
Reverse recovery charge	Q_{rr}			264	476	nC

Notes

(1) Package limited.

(2) Pulse width limited by maximum junction temperature.

(3) V_{DS} = 75 V, V_{GS} = 10 V, L = 0.3 mH.

(4) $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5x1.5 in. board of FR-4 material.

(5) Guaranteed by design, not subject to production testing.

4. Electrical characteristics diagrams

Fig.1 Typ. transfer characteristics

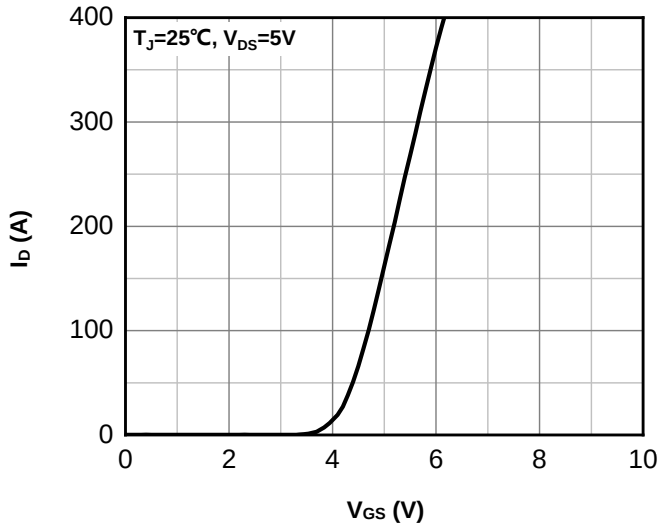


Fig.2 Typ. output characteristics

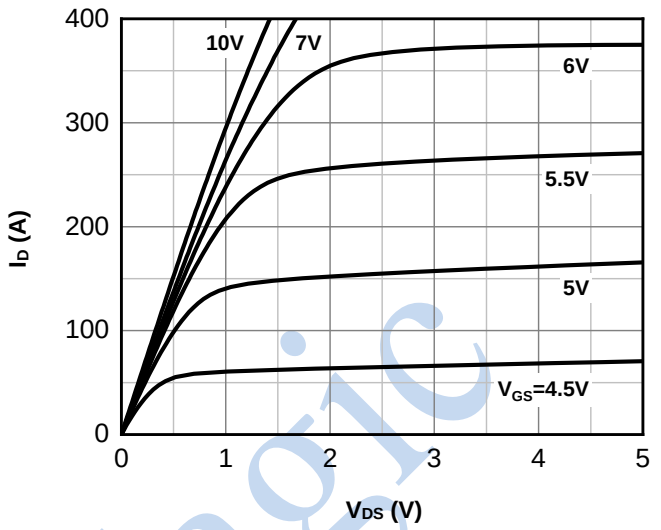


Fig.3 Normalized on-resistance vs drain current

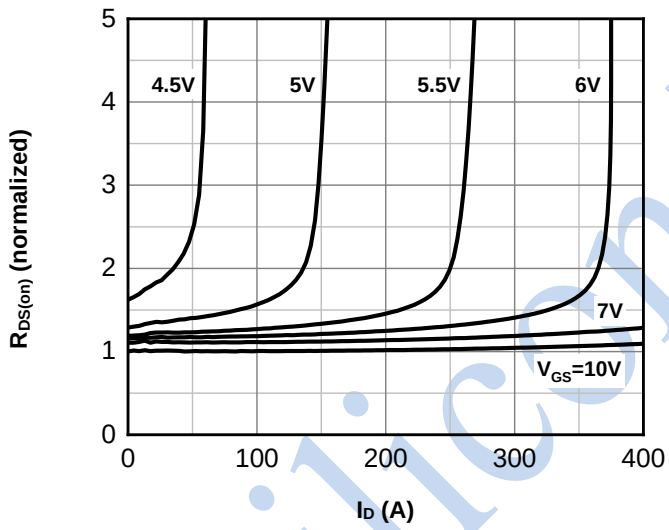


Fig.4 Typ. on-resistance vs gate-source voltage

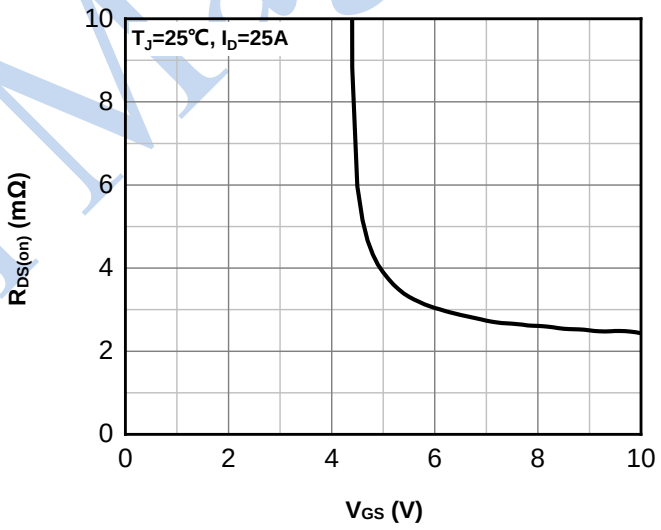


Fig.5 Normalized on-resistance vs junction temperature

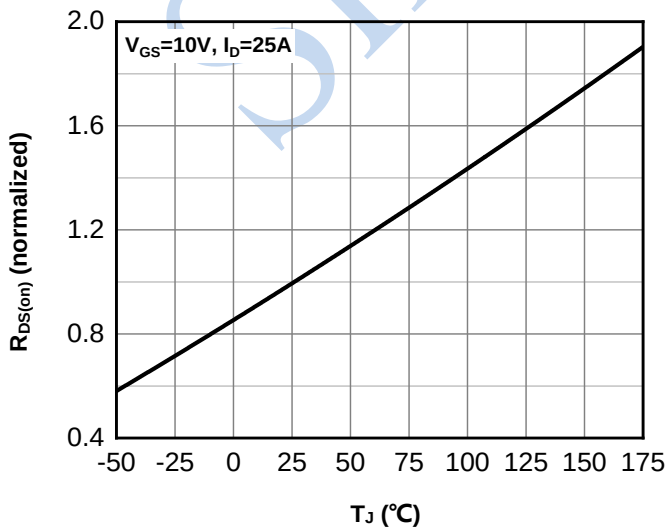


Fig.6 Typ. gate charge

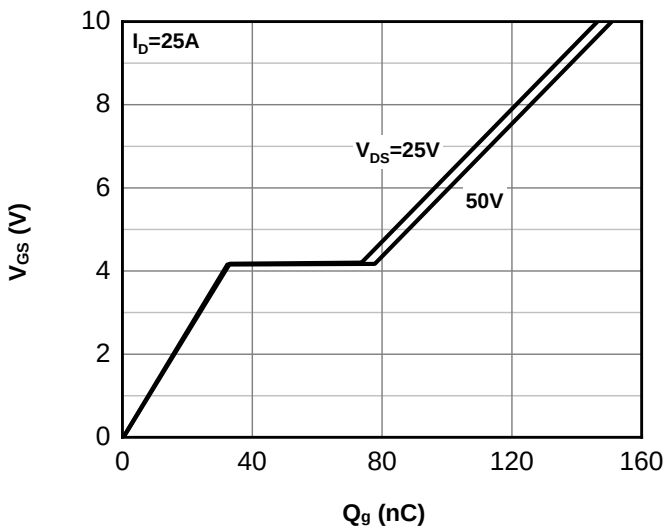


Fig.7 Typ. forward characteristics of body diode

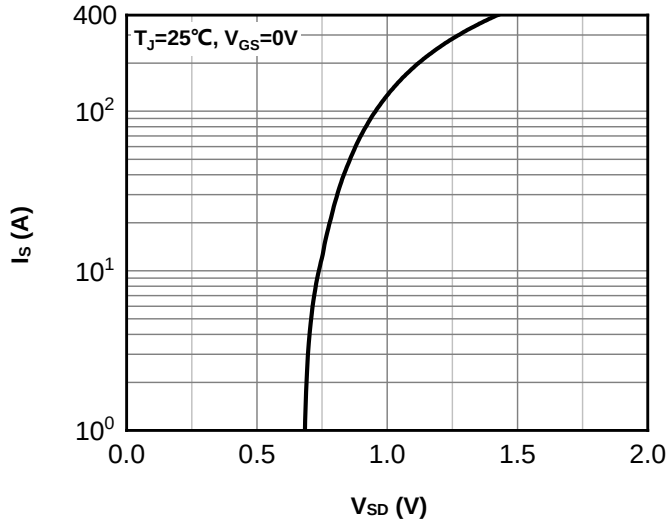


Fig.8 Safe operating area

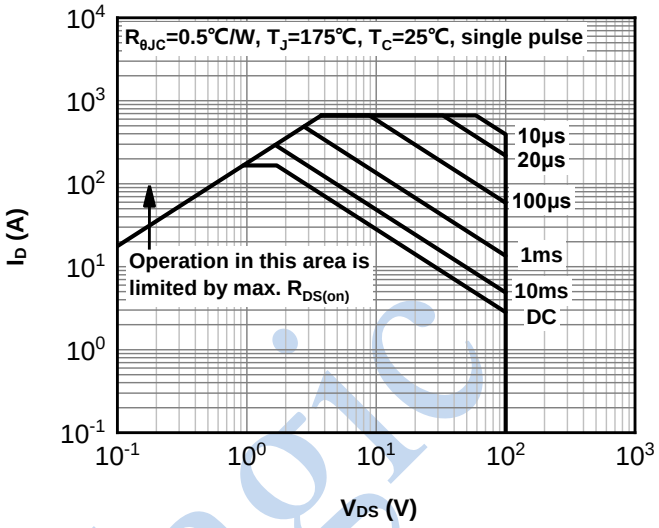


Fig.9 Typ. Capacitance

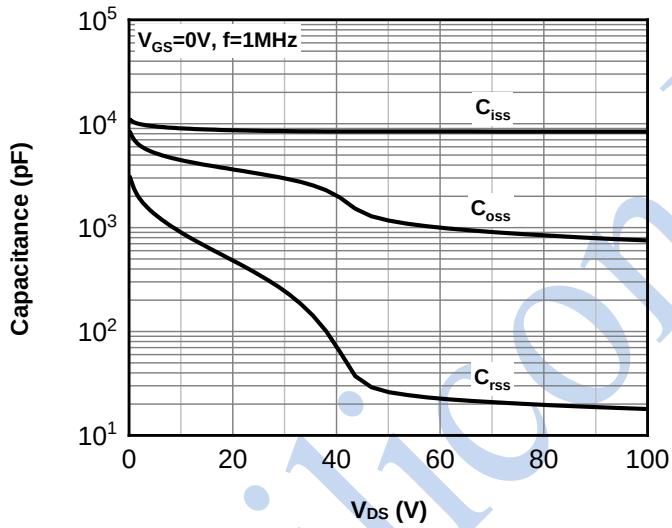


Fig.10 Single pulse maximum power dissipation

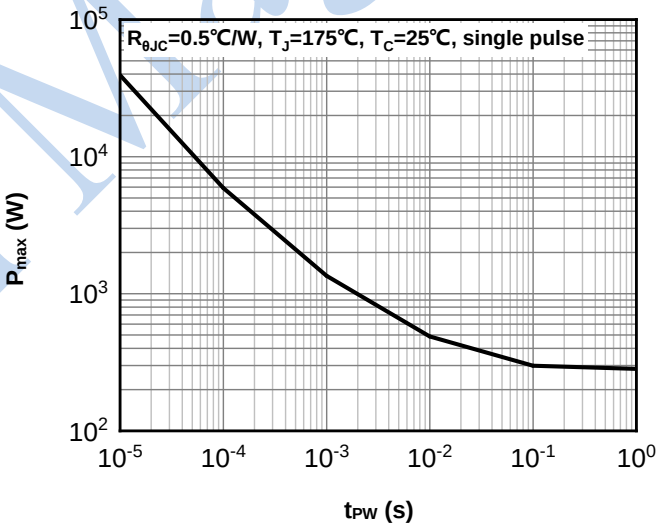


Fig.11 Max. power dissipation vs case temperature

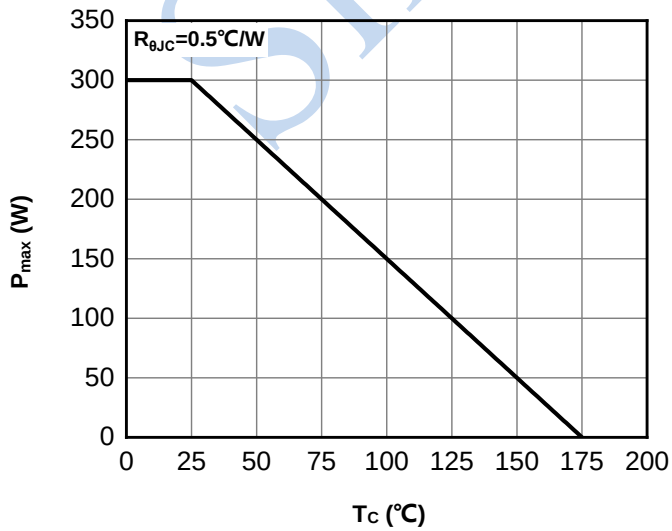


Fig.12 Max. continuous drain current vs case temperature

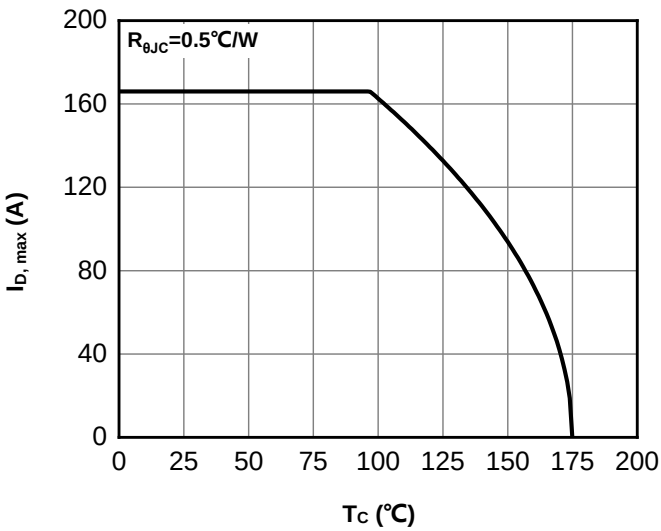
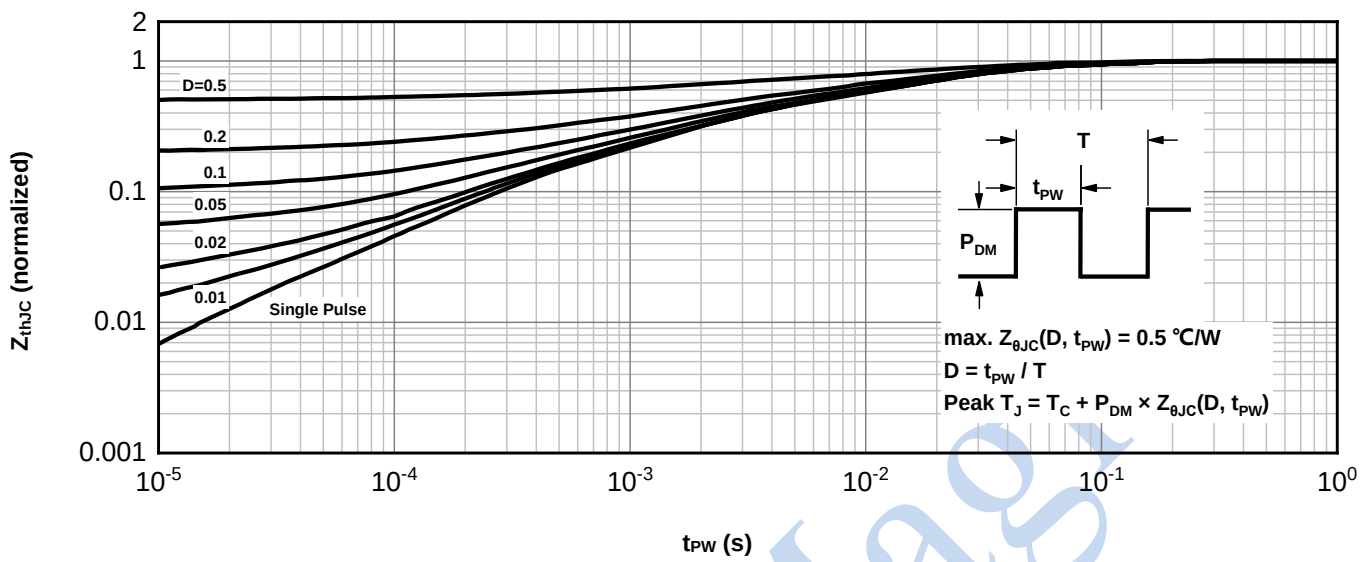
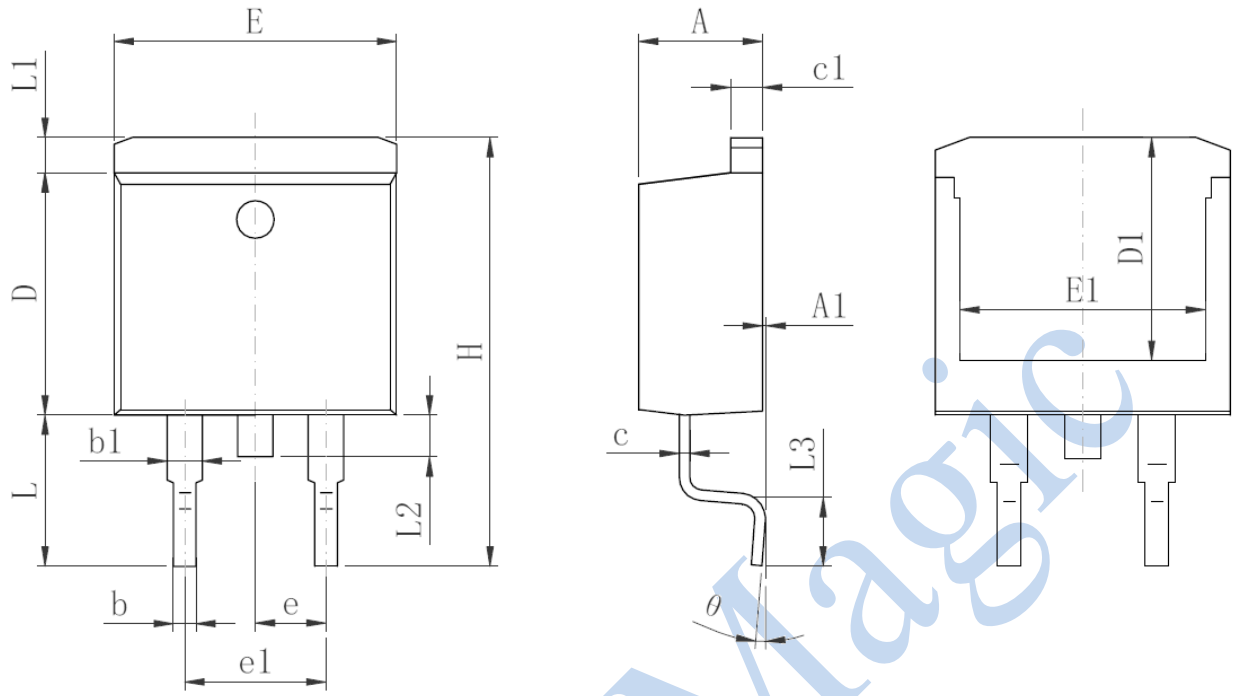


Fig.13 Normalized transient thermal impedance from junction to case



5. Package outline dimensions



Dim	Millimeters		
	Min	Nom	Max
A	4.470	-	4.670
A1	0.000	-	0.150
b	0.710	-	0.910
b1	1.170	-	1.370
c	0.310	-	0.530
c1	1.170	-	1.370
D	8.500	-	8.900
D1	7.670 REF		
E	10.010	-	10.310
E1	8.460 REF		
e	2.540 BSC		
e1	4.980	-	5.180
H	14.940	-	15.500
L	4.950	-	5.450
L1	1.120	-	1.420
L2	1.300	-	1.700
L3	2.340	-	2.740
θ	0°	-	8°

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